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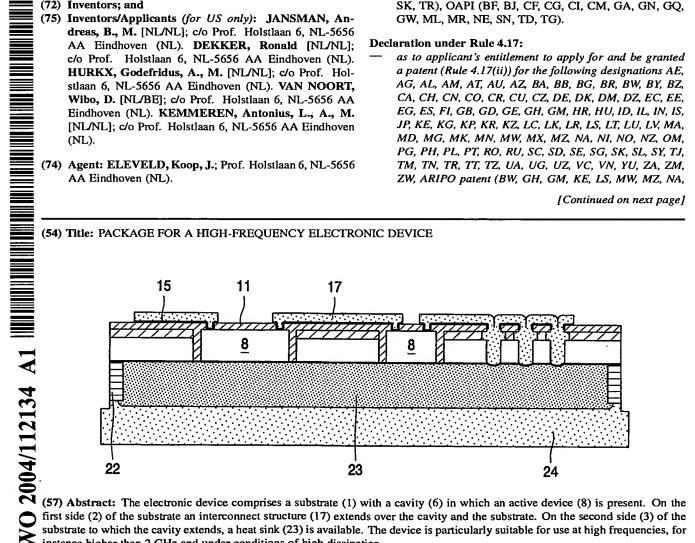
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first side (2) of the substrate an interconnect structure (17) extends over the cavity and the substrate. On the second side (3) of the substrate to which the cavity extends, a heat sink (23) is available. The device is particularly suitable for use at high frequencies, for instance higher than 2 GHz and under conditions of high dissipation.



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